

Product Summary

BV _{DSS}	R _{Ds(ON)}	I _D T _C = +25°C
60V	16mΩ @ V _{GS} = 10V	31A
	24mΩ @ V _{GS} = 4.5V	24A

Description

This new generation n-channel enhancement mode MOSFET is designed to minimize R_{Ds(ON)} yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switches.

Applications

- Motor control
- DC-DC converters
- Power management

Features

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{Ds(ON)} – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

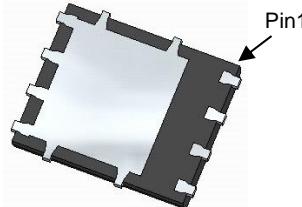
- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

Site 1:

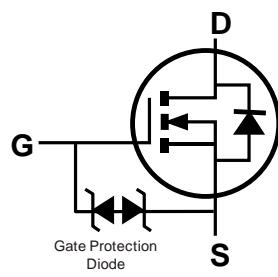
PowerDI5060-8



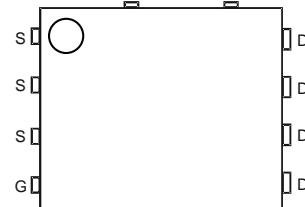
Top View



Bottom View



Internal Schematic



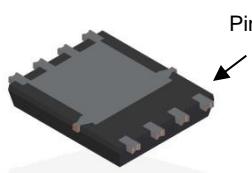
Top View
Pin Configuration

Site 2:

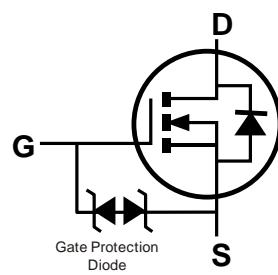
PowerDI5060-8/SWP (Type UX)



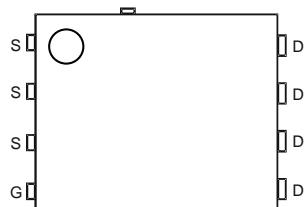
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

Notes:

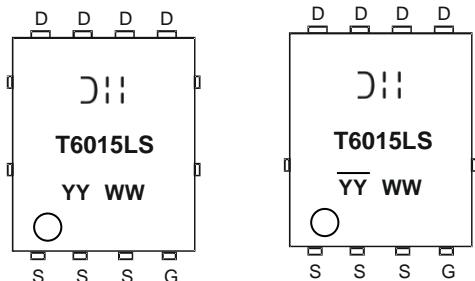
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

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Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMT6015LPS-13	PowerDI5060-8	2,500	Tape & Reel
DMT6015LPS-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


DII = Manufacturer's Marking
 T6015LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Last Two Digits of Year (ex: 25 = 2025)
 WW = Week Code (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 16	V
	$T_A = +25^\circ\text{C}$	I_D	10.6
	$T_A = +70^\circ\text{C}$		8.5
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	$T_c = +25^\circ\text{C}$	I_D	31
	$T_c = +70^\circ\text{C}$		25
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	60	A
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	2	A
Avalanche Current (Note 7) $L=0.1\text{mH}$	I_{AS}	10	A
Avalanche Energy (Note 7) $L=0.1\text{mH}$	E_{AS}	5	mJ
V_{DS} Spike	$t = 10\mu\text{s}$	V_{SPIKE}	75
			V

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.16	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	108	$^\circ\text{C}/\text{W}$
$t < 10\text{s}$		56	
Total Power Dissipation (Note 6)	P_D	2.7	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	46	$^\circ\text{C}/\text{W}$
$t < 10\text{s}$		24	
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	4.4	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$\text{V}_{\text{DS}} = 48\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$\text{V}_{\text{GS}} = \pm 16\text{V}$, $\text{V}_{\text{DS}} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$\text{V}_{\text{GS(TH)}}$	0.5	—	2.5	V	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}$, $\text{I}_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$\text{R}_{\text{DS(ON)}}$	—	14.2	16	$\text{m}\Omega$	$\text{V}_{\text{GS}} = 10\text{V}$, $\text{I}_D = 10\text{A}$
		—	18	24		$\text{V}_{\text{GS}} = 4.5\text{V}$, $\text{I}_D = 6\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1103	—	pF	$\text{V}_{\text{DS}} = 30\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	251.3	—		
Reverse Transfer Capacitance	C_{rss}	—	19.7	—	Ω	$\text{V}_{\text{DS}} = 0\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$, $f = 1\text{MHz}$
Gate Resistance	R_G	—	1.5	—		
Total Gate Charge ($\text{V}_{\text{GS}} = 4.5\text{V}$)	Q_g	—	8.9	—	nC	$\text{V}_{\text{DS}} = 30\text{V}$, $\text{I}_D = 10\text{A}$
Total Gate Charge ($\text{V}_{\text{GS}} = 10\text{V}$)	Q_g	—	18.9	—		
Gate-Source Charge	Q_{gs}	—	3.0	—	ns	$\text{V}_{\text{GS}} = 10\text{V}$, $\text{V}_{\text{DS}} = 30\text{V}$, $\text{R}_G = 6\Omega$, $\text{I}_D = 10\text{A}$
Gate-Drain Charge	Q_{gd}	—	2.8	—		
Turn-On Delay Time	$\text{t}_{\text{D(ON)}}$	—	4.1	—	ns	$\text{V}_{\text{GS}} = 10\text{V}$, $\text{V}_{\text{DS}} = 30\text{V}$, $\text{R}_G = 6\Omega$, $\text{I}_D = 10\text{A}$
Turn-On Rise Time	t_R	—	7.1	—		
Turn-Off Delay Time	$\text{t}_{\text{D(OFF)}}$	—	19.5	—	ns	$\text{I}_F = 10\text{A}$, $\text{di/dt} = 100\text{A}/\mu\text{s}$
Turn-Off Fall Time	t_F	—	8.6	—		
Reverse-Recovery Time	t_{RR}	—	21.2	—	nC	$\text{I}_F = 10\text{A}$, $\text{di/dt} = 100\text{A}/\mu\text{s}$
Reverse-Recovery Charge	Q_{RR}	—	13.2	—		

Notes: 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

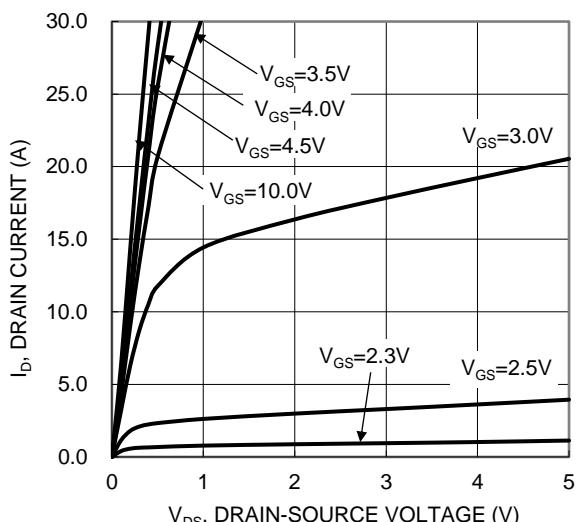


Figure 1. Typical Output Characteristic

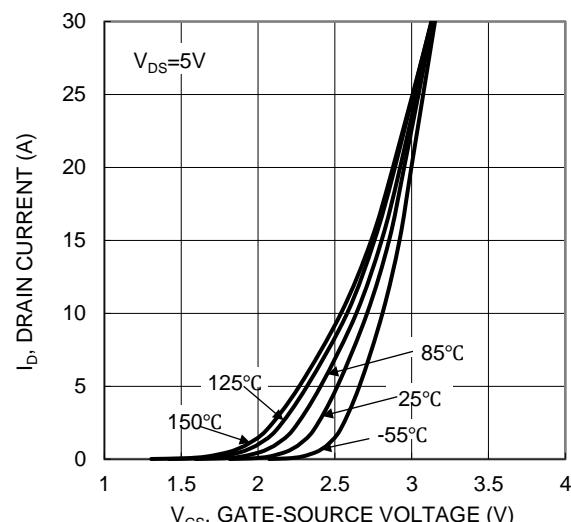


Figure 2. Typical Transfer Characteristic

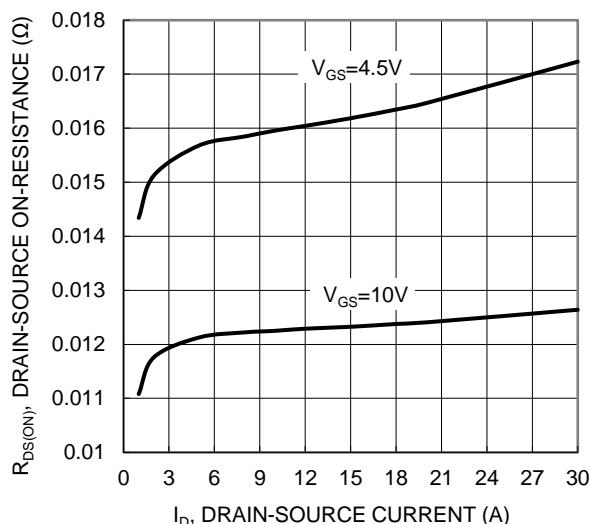


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

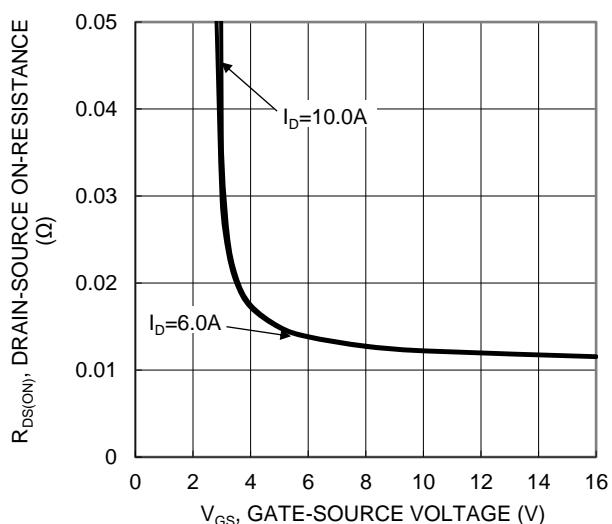


Figure 4. Typical Transfer Characteristic

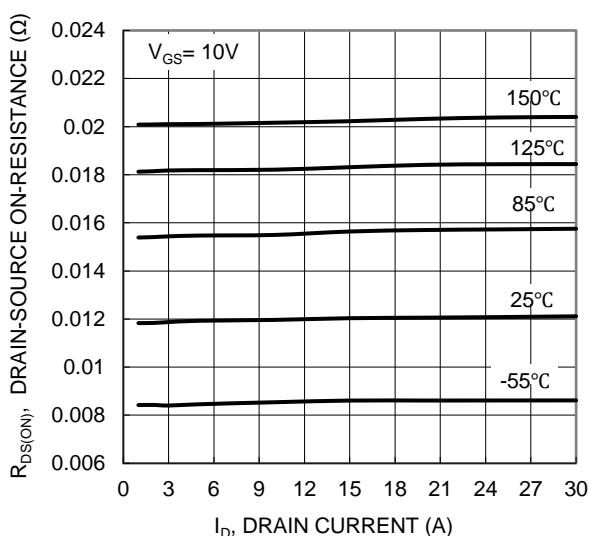


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

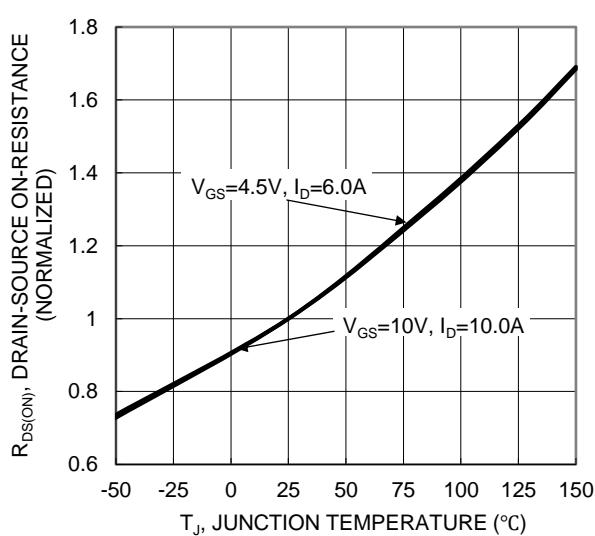


Figure 6. On-Resistance Variation with Temperature

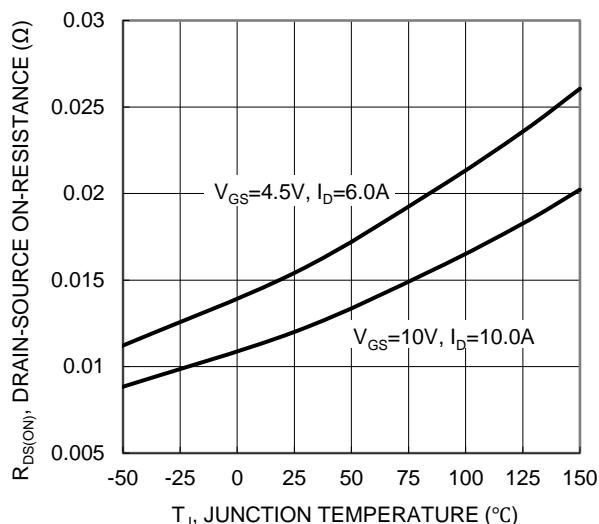


Figure 7. On-Resistance Variation with Temperature

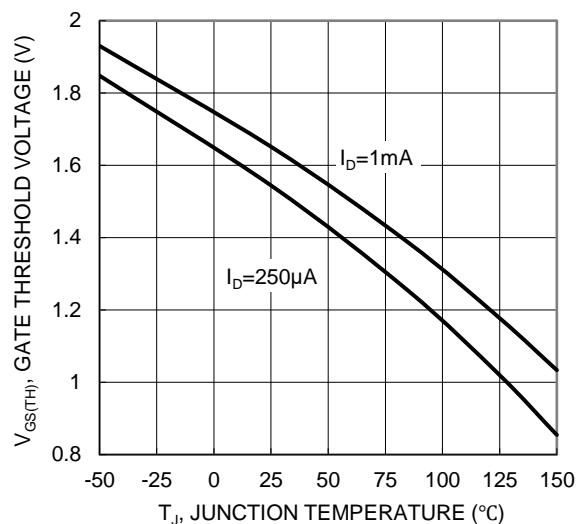


Figure 8. Gate Threshold Variation vs. Temperature

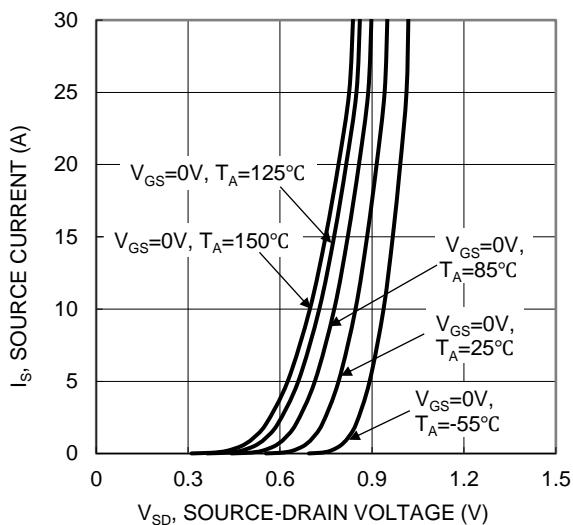


Figure 9. Diode Forward Voltage vs. Current

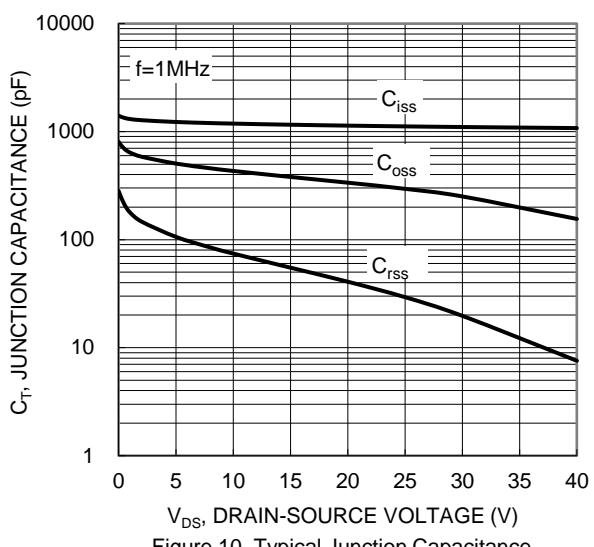


Figure 10. Typical Junction Capacitance

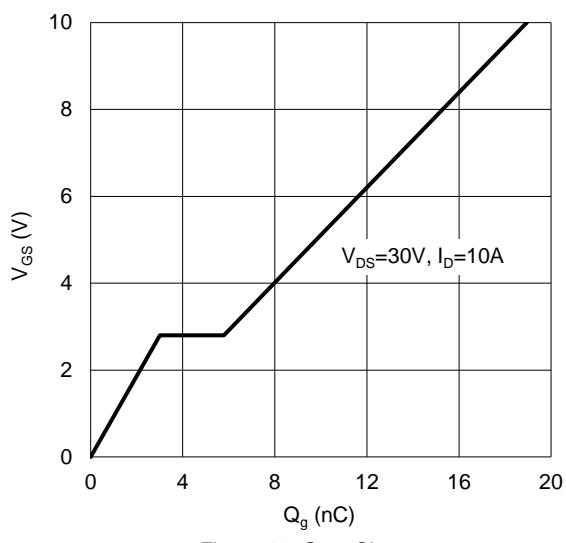


Figure 11. Gate Charge

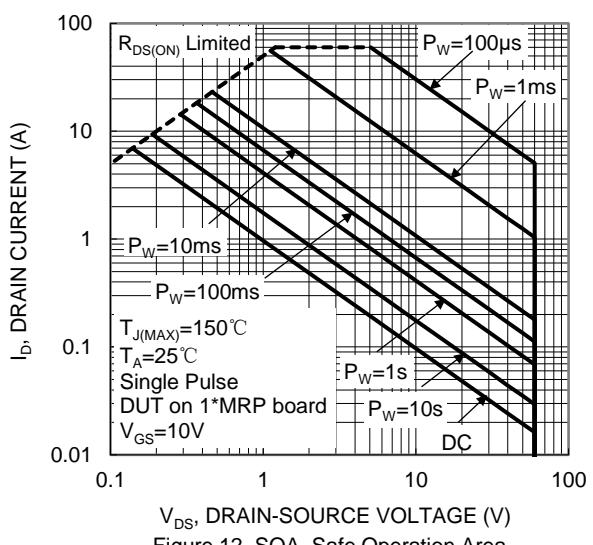


Figure 12. SOA, Safe Operation Area

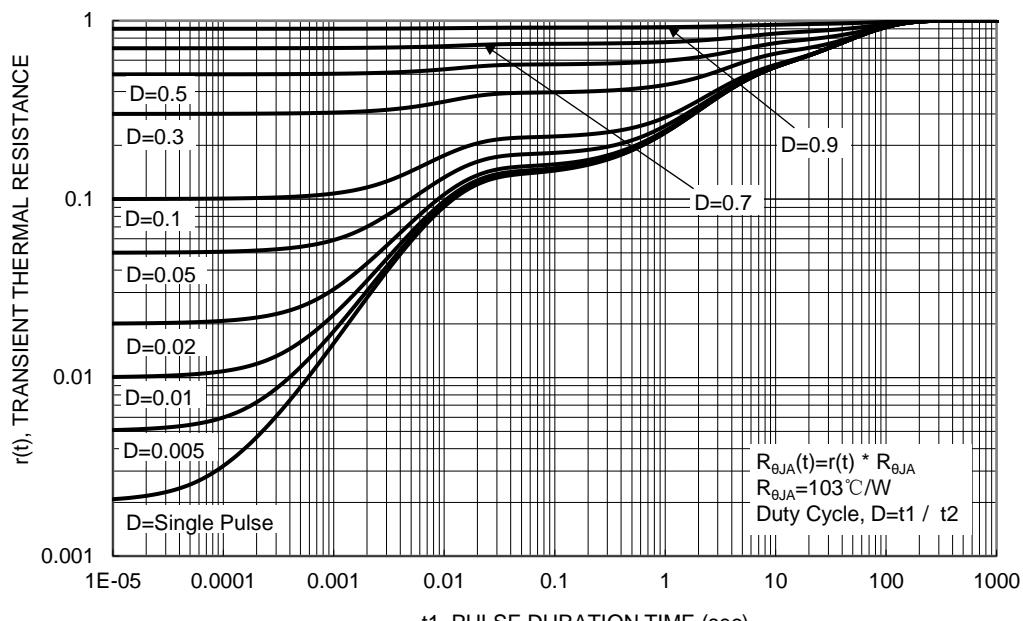


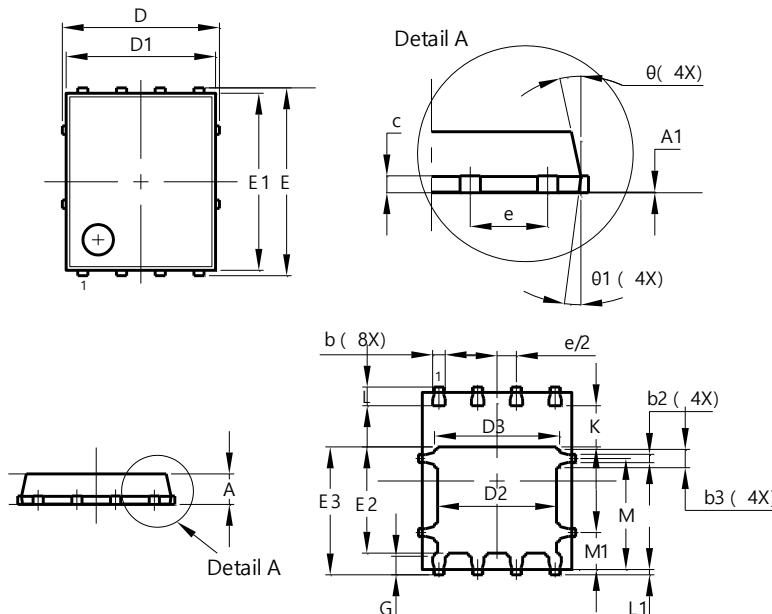
Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

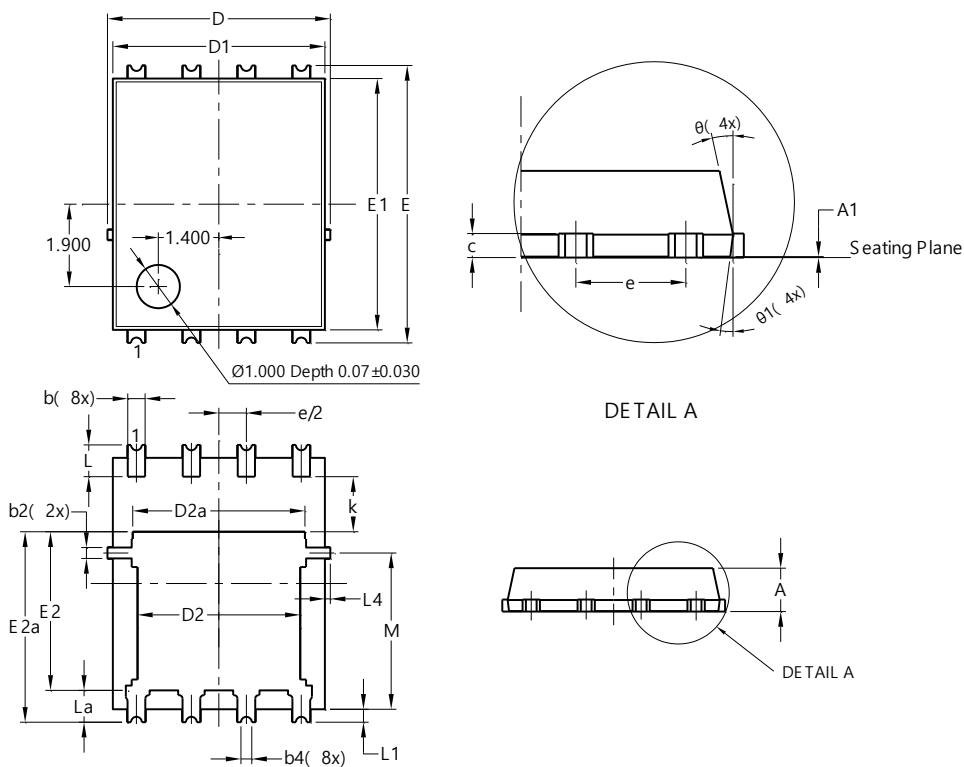
PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
Θ	10°	12°	11°
Θ1	6°	8°	7°

Site 2:

PowerDI5060-8/SWP (Type UX)



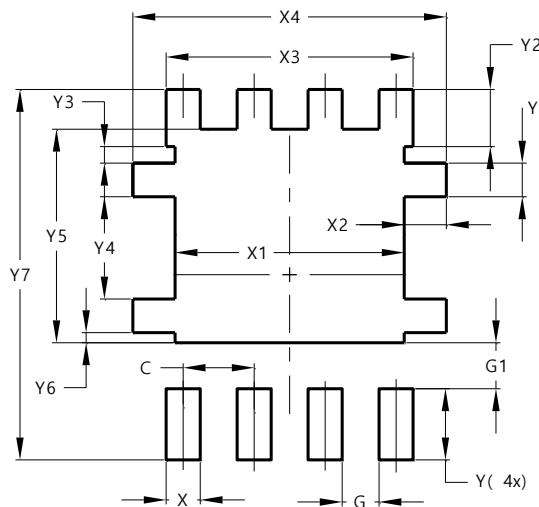
PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

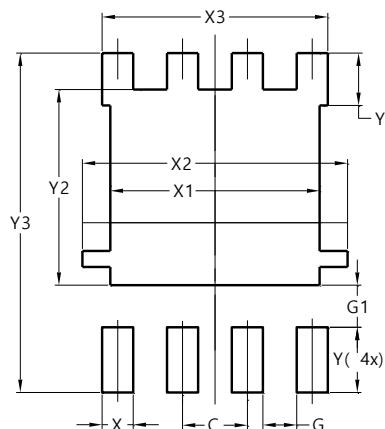
PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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